
2SK2217

Silicon N-Channel MOS FET

HITACHI

ADE-208-347A
2nd. Edition

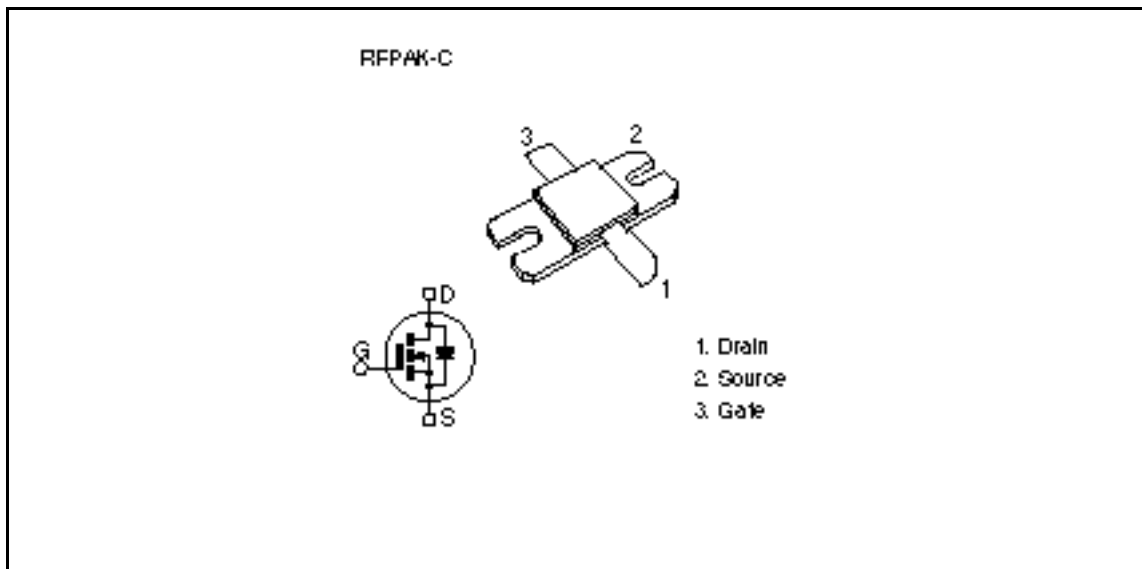
Application

UHF power amplifier

Features

- Σ High power output, high gain, high efficiency
PG = 10 dB, Pout = 60 W, hD = 55% typ (f = 860 MHz)
- Σ Compact package

Outline



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Absolute Maximum Ratings (Ta = 25°C)

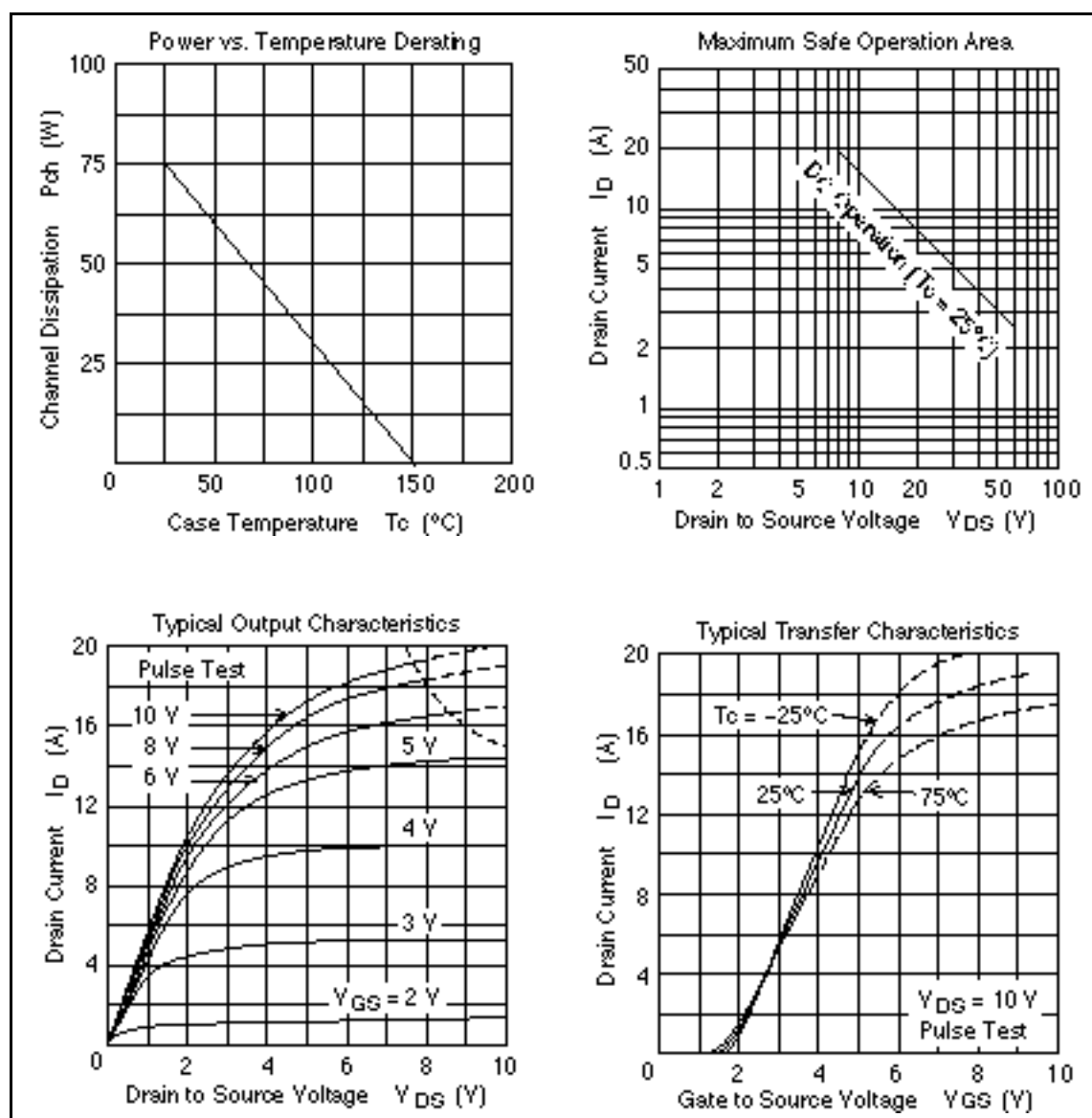
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±10	V
Drain current	I_D	10	A
Channel dissipation	Pch* ¹	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

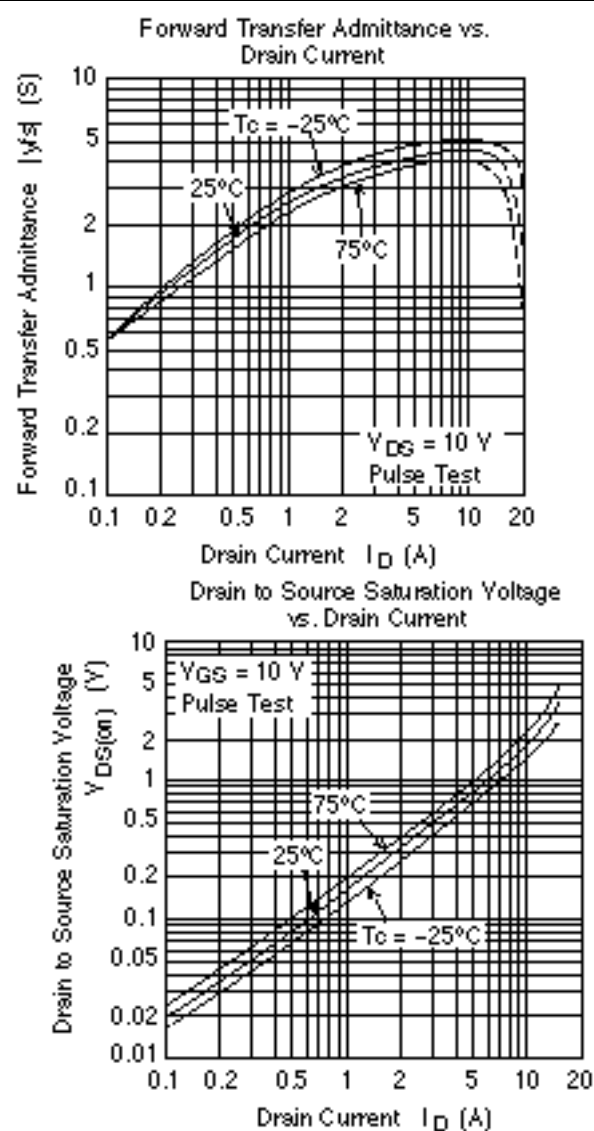
Note: 1. Value at T_c = 25°C

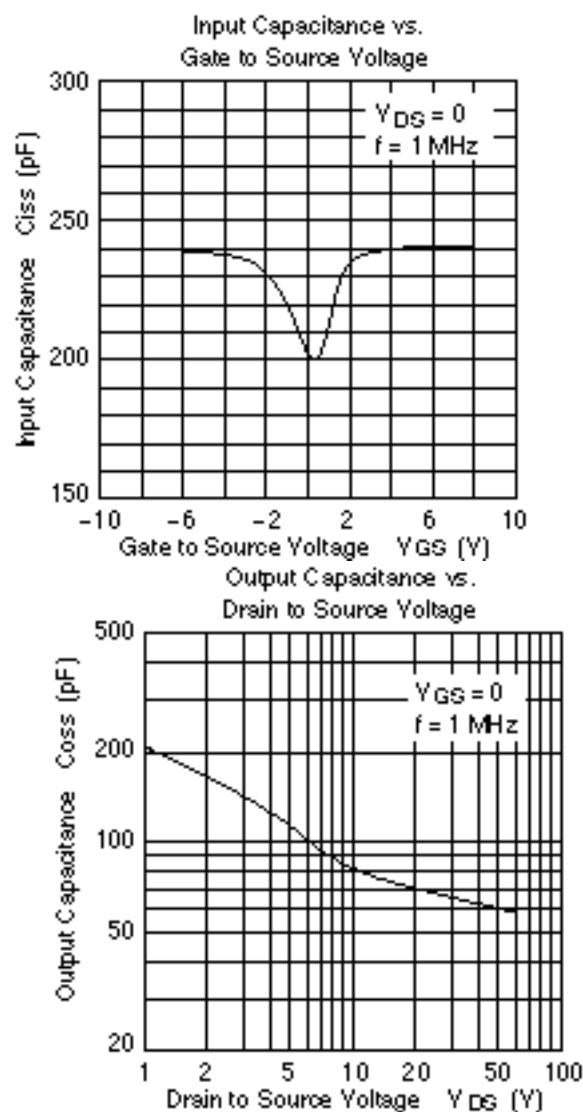
Electrical Characteristics (T_c = 25°C)

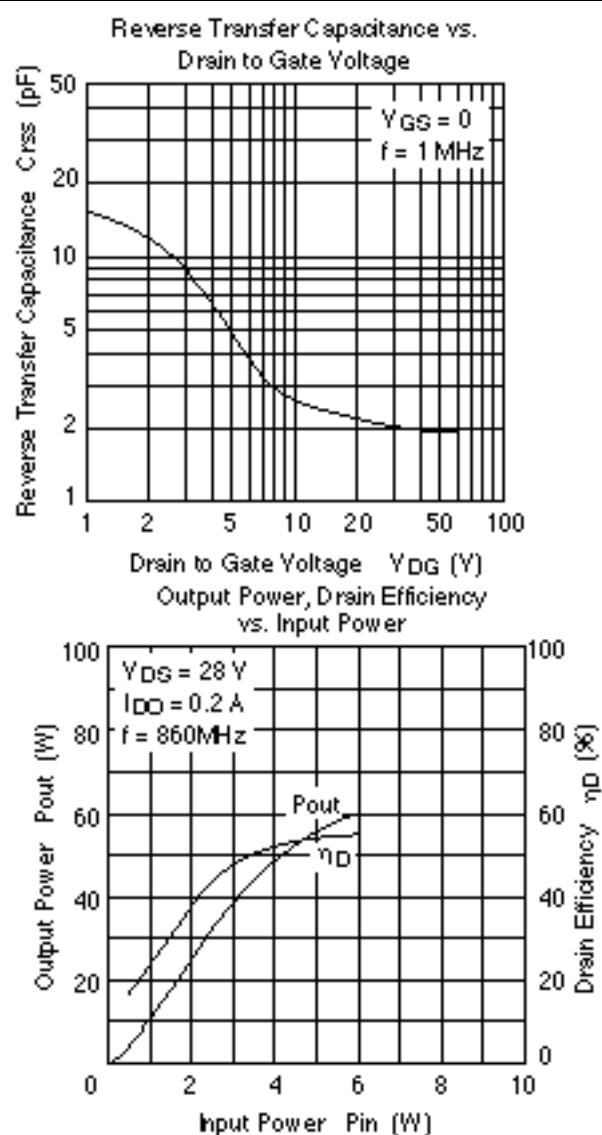
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain leakage current	I_{DSS}	—	—	1	mA	$V_{DS} = 60\text{ V}, V_{GS} = 0$
Gate leakage current	I_{GSS}	—	—	± 3	μA	$V_{GS} = \pm 10\text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.3	—	1.6	V	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$
Drain to source voltage	$V_{DS(on)}$	—	1.2	2.5	V	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.0	4.0	—	S	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}^{*1}$
Input capacitance	Ciss	—	250	—	pF	$V_{GS} = 5\text{ V}, V_{DS} = 0$ f = 1MHz
Output capacitance	Coss	—	85	—	pF	$V_{DS} = 10\text{ V}, V_{GS} = 0$ f = 1MHz
Output power	P _{OUT}	40	60	—	W	$V_{DS} = 28\text{ V}, I_{DO} = 0.2\text{ A}$
Drain efficiency	hD	—	55	—	%	f = 860 MHz, Pin = 6 W

Note: 1. Pulse Test



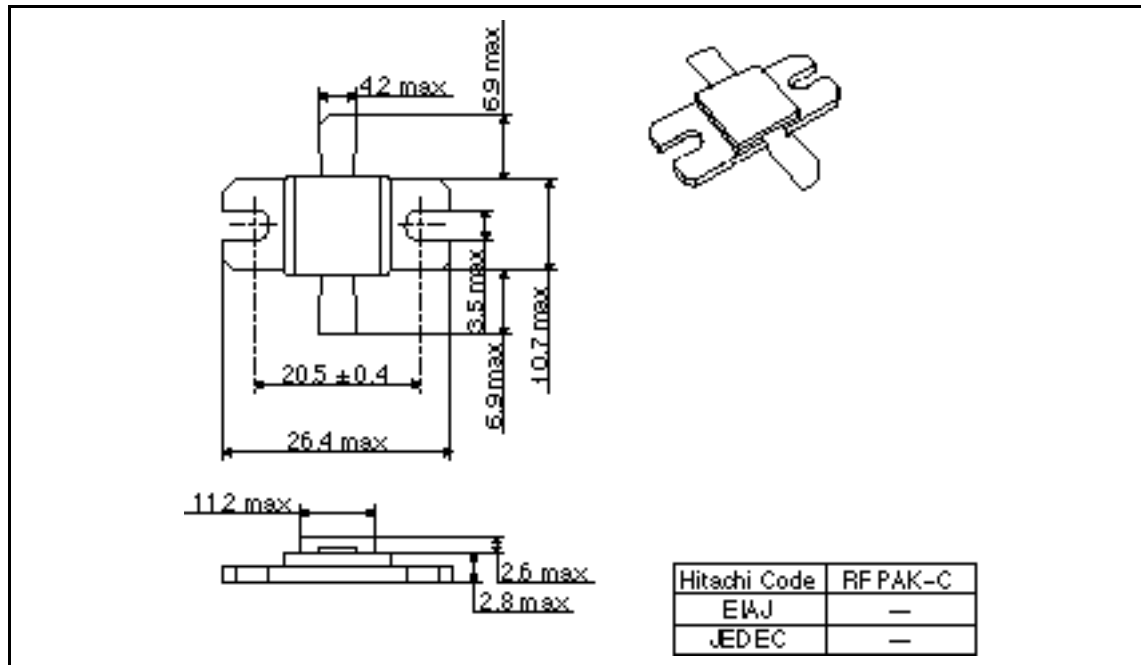






Package Dimensions

Unit: mm



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